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In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

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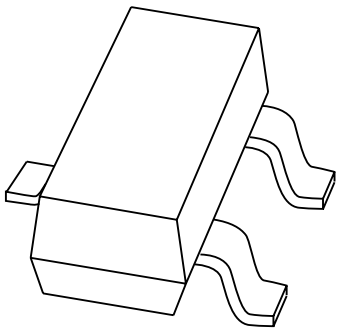
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



PBSS4130T

30 V, 1 A
NPN low V_{CEsat} (BISS) transistor

Product specification

2003 Nov 27

Philips
Semiconductors

PHILIPS

30 V, 1 A NPN low V_{CEsat} (BISS) transistor

PBSS4130T

FEATURES

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- Cost effective alternative to MOSFETs in specific applications.

APPLICATIONS

- Power management
  - DC/DC conversion
  - Supply line switching
  - Battery charger
  - LCD backlighting.
- Peripheral driver
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load drivers (e.g. relays, buzzers and motors).

DESCRIPTION

NPN BISS transistor in a SOT23 plastic package providing ultra low V_{CEsat} and R_{CEsat} parameters.
PNP complement: PBSS5130T.

MARKING

TYPE NUMBER	MARKING CODE(1)
PBSS4130T	*3C

Note

1. * = p: made in Hong Kong.
   * = t: made in Malaysia.
   * = W: made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	30	V
I_C	collector current (DC)	1	A
I_{CM}	peak collector current	3	A
R_{CEsat}	equivalent on-resistance	220	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

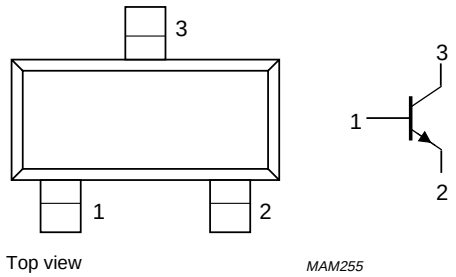


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS4130T	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	30	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	1	A
I_{CM}	peak collector current		–	3	A
I_{BM}	peak base current		–	300	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	300	mW
		$T_{amb} \leq 25$ °C; note 2	–	480	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Notes

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

Notes

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm^2.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

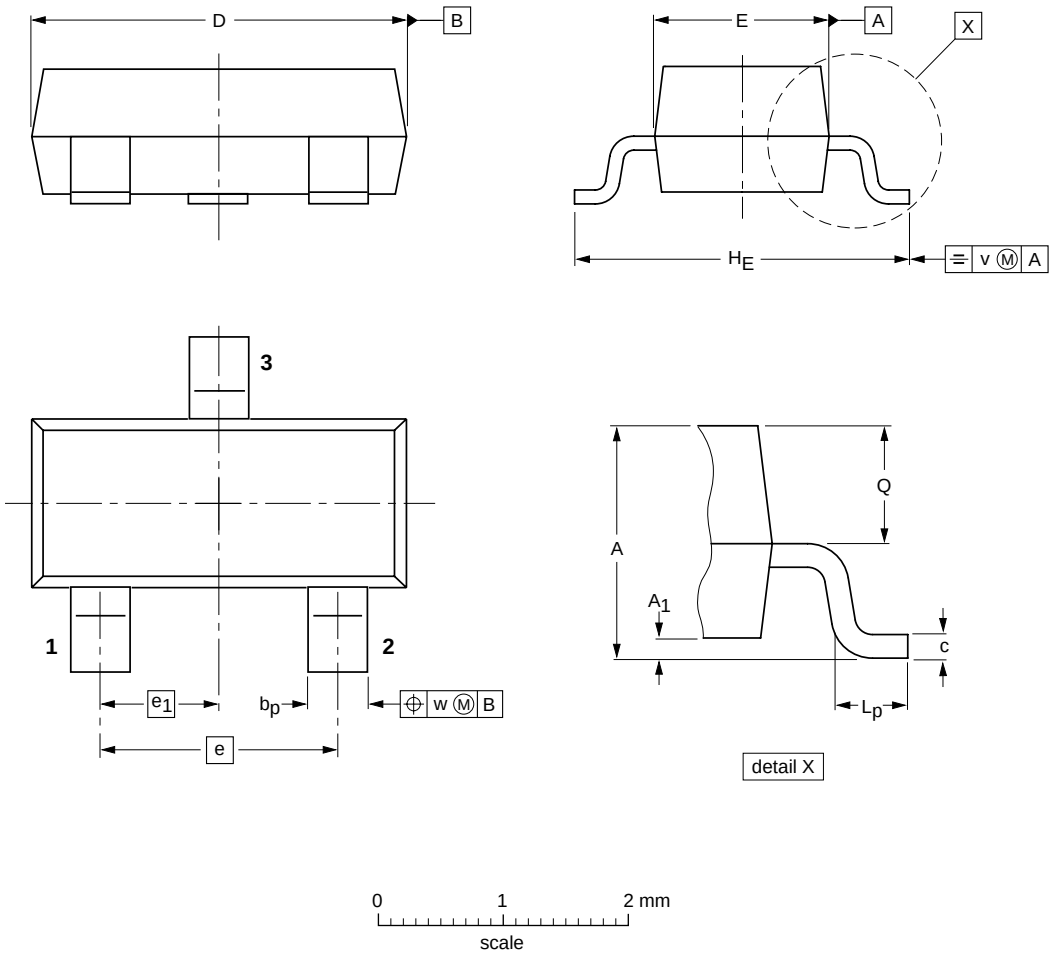
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = 30 V; I_E = 0	–	–	100	nA
		V_{CB} = 30 V; I_E = 0; T_j = 150 °C	–	–	50	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = 4 V; I_C = 0	–	–	100	nA
h_{FE}	DC current gain	V_{CE} = 2 V; I_C = 100 mA	350	470	–	
		V_{CE} = 2 V; I_C = 500 mA	300	450	–	
		V_{CE} = 2 V; I_C = 1 A	300	420	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = 100 mA; I_B = 1 mA	–	–	90	mV
		I_C = 500 mA; I_B = 50 mA	–	–	120	mV
		I_C = 750 mA; I_B = 15 mA	–	–	220	mV
		I_C = 1 A; I_B = 50 mA; note 1	–	–	270	mV
R_{CEsat}	equivalent on-resistance	I_C = 500 mA; I_B = 50 mA; note 1	–	–	240	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA; note 1	–	–	1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_C = 100 mA	–	–	0.75	V
f_T	transition frequency	I_C = 100 mA; V_{CE} = 10 V; f = 100 MHz	100	–	–	MHz
C_c	collector capacitance	V_{CB} = 10 V; I_E = I_e = 0; f = 1 MHz	–	–	20	pF

Note

1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				~~97-02-28~~ 99-09-13

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

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DEFINITIONS

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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